

NTMYS010N04CL

Power MOSFET 40 V, 10.3 mΩ, 38 A, Single N-Channel

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- LFPACK4 Package, Industry Standard
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	40	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3)	$T_C = 25^\circ\text{C}$	I_D	38
			27
Power Dissipation $R_{\theta JC}$ (Notes 1, 2)	$T_C = 25^\circ\text{C}$	P_D	28
			14
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	$T_A = 25^\circ\text{C}$	I_D	14
			9.9
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	$T_A = 25^\circ\text{C}$	P_D	3.8
			1.9
Pulsed Drain Current	$T_A = 25^\circ\text{C}$, $t_p = 10\ \mu\text{s}$	I_{DM}	187
Operating Junction and Storage Temperature	T_J , T_{stg}	-55 to + 175	°C
Source Current (Body Diode)	I_S	24	A
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}$, $I_{L(pk)} = 1.9\text{ A}$)	E_{AS}	62	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	5.3	°C/W
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	39	

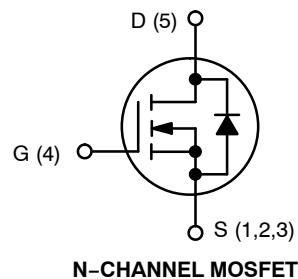
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



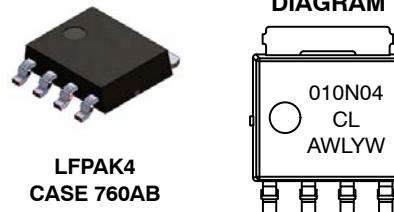
ON Semiconductor®

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$V_{(BR)DSS}$	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
40 V	10.3 mΩ @ 10 V	38 A
	17.6 mΩ @ 4.5 V	



N-CHANNEL MOSFET



LFPACK4
CASE 760AB

010N04CL = Specific Device Code

A = Assembly Location

WL = Wafer Lot

Y = Year

W = Work Week

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NTMYS010N04CL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA		40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J				24		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 40 V	T _J = 25°C			10	μA
			T _J = 125°C			250	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V				100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 20 μA		1.2		2.0	V
Threshold Temperature Coefficient	V _{GS(TH)} /T _J				-5.5		mV/°C
Drain-to-Source On Resistance	R _{DSS(on)}	V _{GS} = 10 V	I _D = 20 A		8.6	10.3	mΩ
		V _{GS} = 4.5 V	I _D = 20 A		14.5	17.6	
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 20 A			33		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 25 V		570		pF
Output Capacitance	C _{OSS}			230		
Reverse Transfer Capacitance	C _{rss}			11		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 20 V; I _D = 20 A		7.3		nC
Total Gate Charge	Q _{G(TOT)}			3.4		
Threshold Gate Charge	Q _{G(TH)}			0.9		
Gate-to-Source Charge	Q _{GS}			1.6		
Gate-to-Drain Charge	Q _{GD}			1.0		
Plateau Voltage	V _{GP}			3.4		
						V

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DS} = 20 V, I _D = 20 A, R _G = 1 Ω		7		ns
Rise Time	t _r			43		
Turn-Off Delay Time	t _{d(OFF)}			11		
Fall Time	t _f			2		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 20 A	T _J = 25°C		0.88	1.2	V
			T _J = 125°C		0.79		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 20 A			18		ns
Charge Time	t _a				9		
Discharge Time	t _b				9		
Reverse Recovery Charge	Q _{RR}				6.0		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

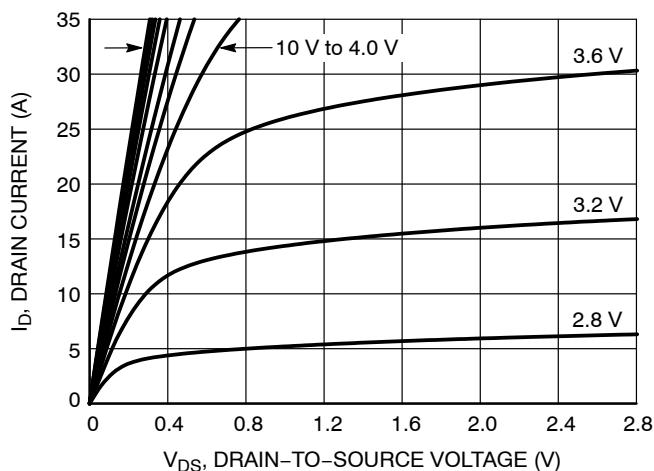


Figure 1. On-Region Characteristics

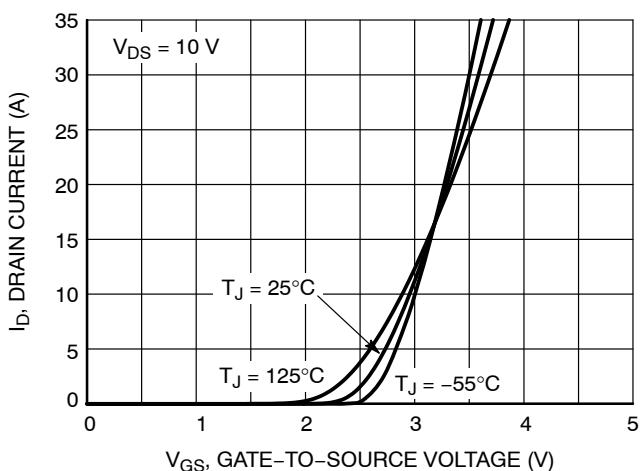


Figure 2. Transfer Characteristics

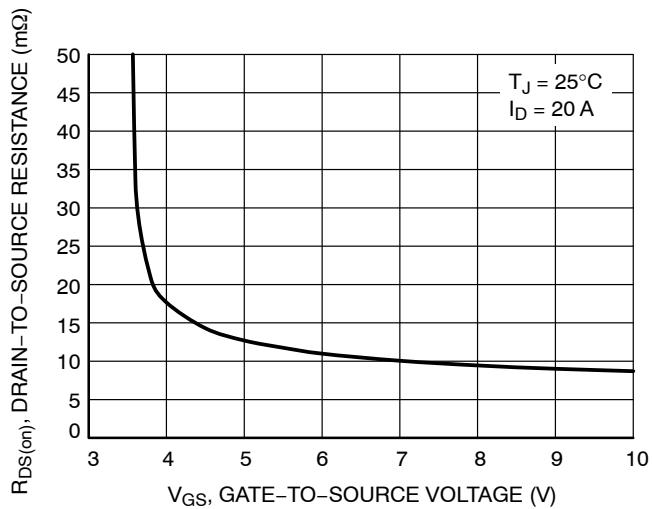


Figure 3. On-Resistance vs. Gate-to-Source Voltage

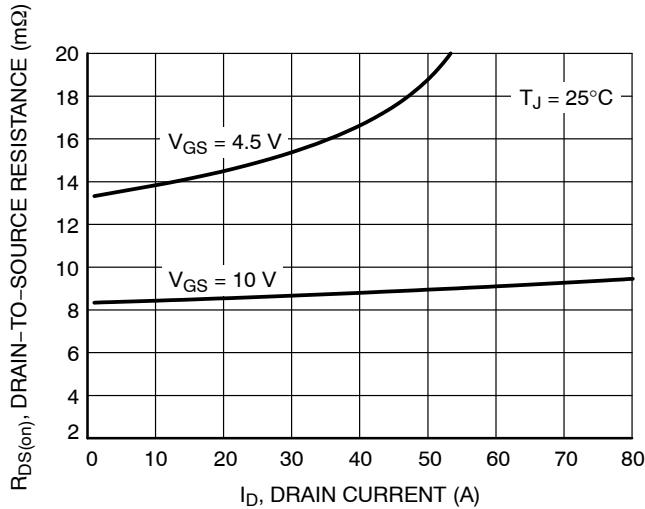


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

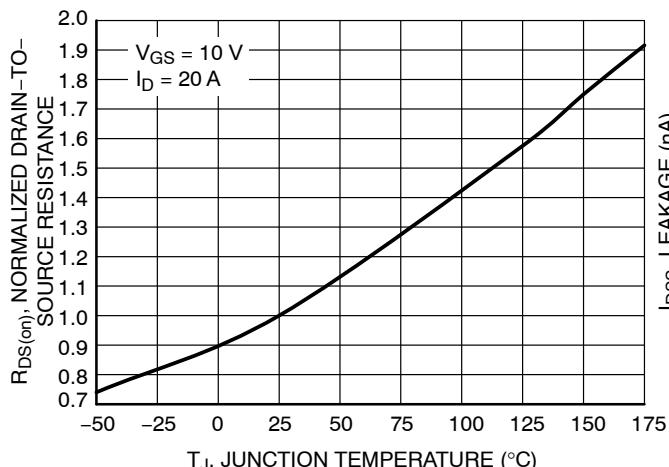


Figure 5. On-Resistance Variation with Temperature

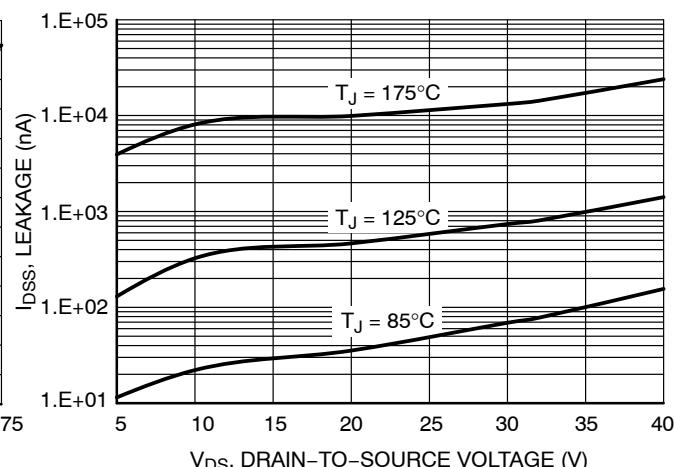


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

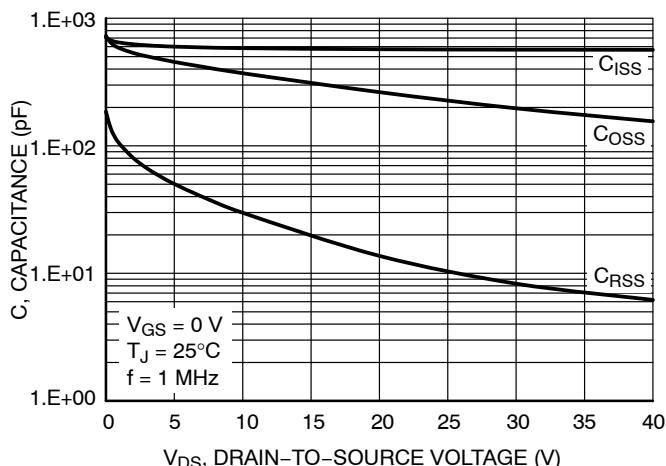


Figure 7. Capacitance Variation

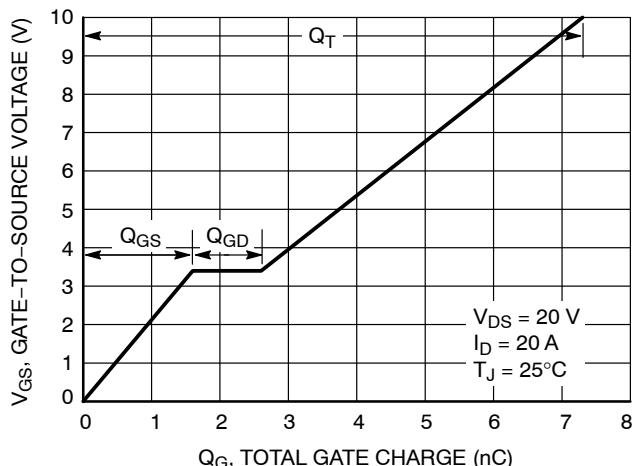


Figure 8. Gate-to-Source vs. Total Charge

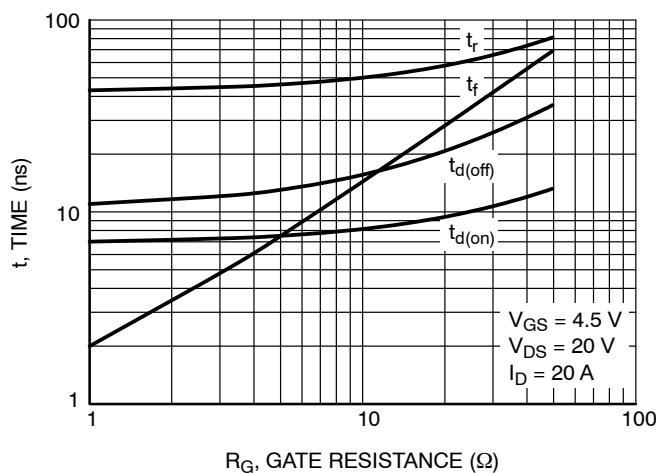


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

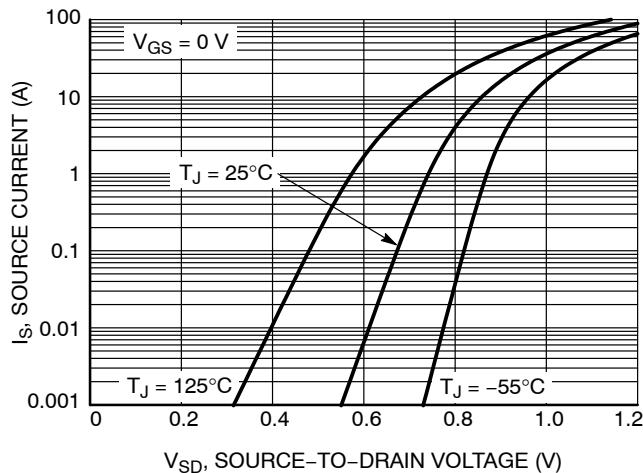


Figure 10. Diode Forward Voltage vs. Current

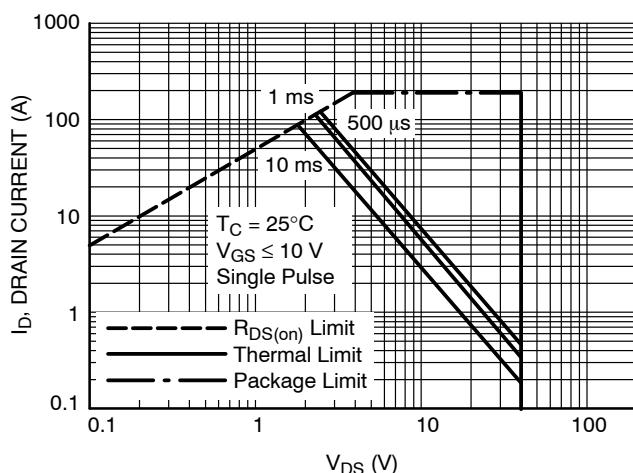
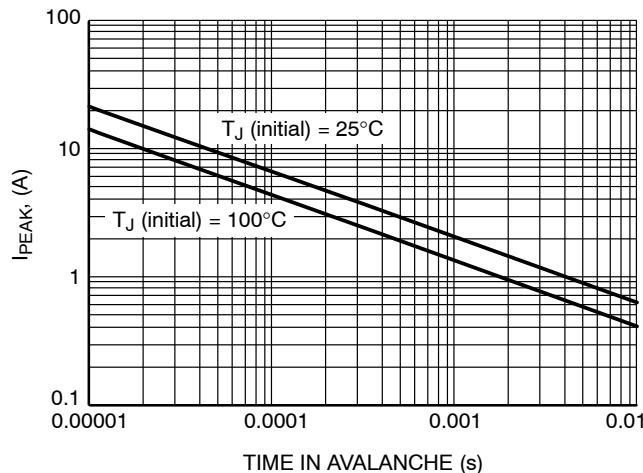


Figure 11. Safe Operating Area

Figure 12. I_{PEAK} vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

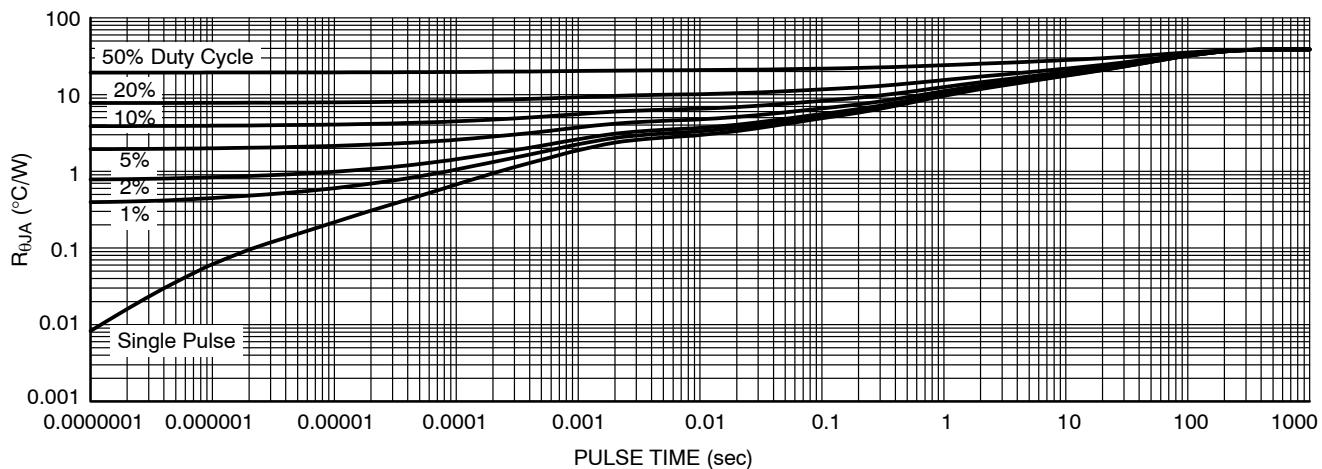


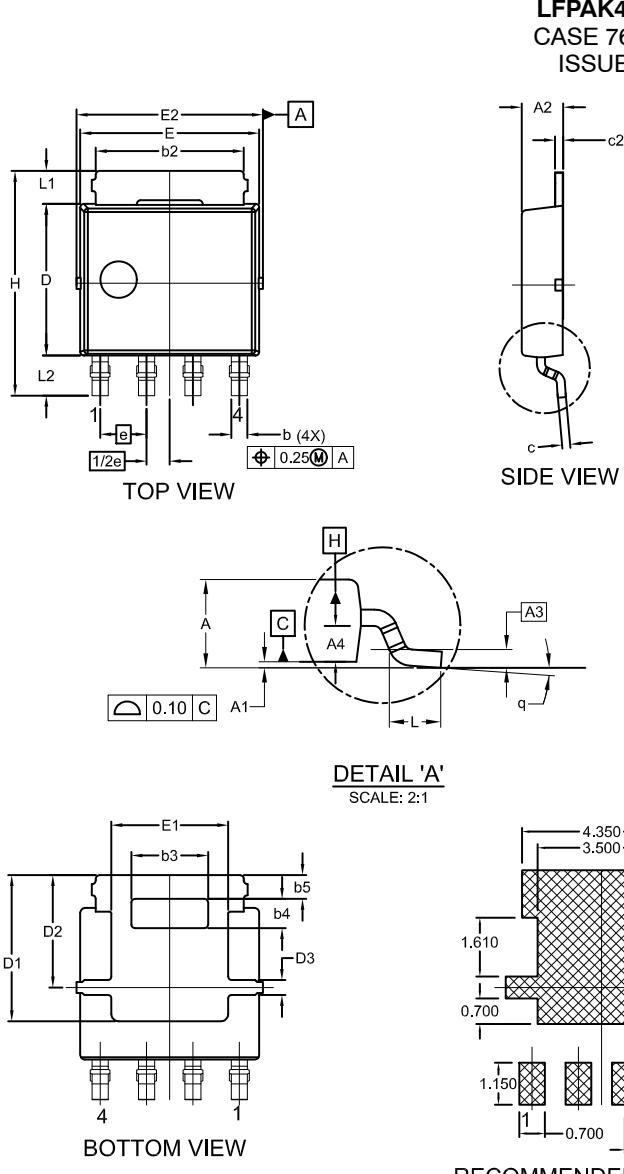
Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NTMYS010N04CLTWG	010N04CL	LFPAK4 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS



LFPK4 5x6
CASE 760AB
ISSUE B

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

UNIT IN MILLIMETER			
DIM	MIN	NOM	MAX
A	1.10	1.20	1.30
A1	0.00	0.08	0.15
A2	1.10	1.15	1.20
A3	0.25		
A4	0.45	0.50	0.55
b	0.40	0.45	0.50
b2	3.80	4.10	4.40
b3	2.00	2.10	2.20
b4	0.70	0.80	0.90
b5	0.55	0.65	0.75
c	0.19	0.22	0.25
c2	0.19	0.22	0.25
D	4.05	4.15	4.25
D1	3.80	4.00	4.20
D2	3.00	3.10	3.20
D3	0.30	0.40	0.50
E	4.80	4.90	5.00
E1	3.10	3.20	3.30
E2	5.00	5.15	5.30
e	1.27	BSC	
H	6.00	6.15	6.30
L	0.40	0.65	0.85
L1	0.80	0.90	1.00
L2	0.80	1.05	1.30
q	0°	4°	8°

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